

MOSFET – Single P-Channel, Small Signal, SOT-1123, 1.0 x 0.6 mm -20 V, -200 mA

NTNUS3171PZ

Features

- Single P-Channel MOSFET
- Offers a Low $R_{DS(on)}$ Solution in the Ultra Small 1.0 x 0.6 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb-Free Device

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	-20	Δ,
Gate-to-Source Voltage	V _{GS}	±8	V
	FID	-150 -110 -200	mA
Power Dissipation (Note 1) Steady State $T_A = 25^{\circ}C$	S _{PD}	-125 -200	mW
Pulsed Drain Current $t_p = 10 \mu s$	I _{DM}	-600	mA
Operating Junction and Storage Temperature	T _J , T _{STG}	–55 to 150	°C
Source Current (Body Diode) (Note 2)	I _S	-200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

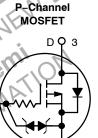
V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max
–20 V	3.5 Ω @ -4.5 V	
	4.0 Ω @ -2.5 V	0.00 4
	5.5 Ω @ -1.8 V	-0.20 A
	7.0 Ω @ -1.5 V	



MARKING DIAGRAM



5 = Specific Device Code (Rotated 90° Clockwise) M = Date Code



ORDERING INFORMATION

Device	Package	Shipping [†]
NTNUS3171PZT5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTNUS3171PZ

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ heta JA}$	1000	°C/W
Junction-to-Ambient - t = 5 s (Note 3)	$R_{ hetaJA}$	600	

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS					•		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -5.0 V T _J = 25°C				-50	
		$V_{GS} = 0 \text{ V}, V_{DS} = -5.0 \text{ V}$	T _J = 85°C			-100	nA
		V _{GS} = 0 V, V _{DS} = -16 V	T _J = 25°C			-200	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±	±5.0 V			±100	nA
ON CHARACTERISTICS (Note 4)					1,0		
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = -2$	250 μΑ	-0.4	+0.7	-1.0	V
Drain-to-Source On Resistance	R _{DS(ON)}	$V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ V}$	100 mA	1/4	2.0	3.5	
		$V_{GS} = -2.5 \text{ V}, I_D = -$	-50 mA		2.6	4.0	
		V _{GS} = -1.8 V, I _D = -	-20 mA		3.4	5.5	Ω
		$V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$		110	4.0	7.0	
		$V_{GS} = -1.2 \text{ V}, I_D = -$	1.0 mA	7,	6.0		
Forward Transconductance	9 FS	$V_{DS} = -5.0 \text{ V, } I_{D} = -$	125 mA		0.26		S
Source-Drain Diode Voltage	V _{SD}	$V_{GS} = 0 \text{ V}, I_{S} = -20$	00 mA	-0.5		-1.4	V
CHARGES, CAPACITANCES AND GATE R	ESISTANCE	0, C, S					
Input Capacitance	C _{ISS}	JAN 501			13		
Output Capacitance	c _{oss}	f = 1 MHz, V _{GS} = 0 V V _{DS} = -15 V			3.4		pF
Reverse Transfer Capacitance	C _{RSS}				1.6		
Total Gate Charge	$Q_{G(TOT)}$	1			0.7		
Threshold Gate Charge	Q _{G(TH)}	\/ 45\/\/ 45\/\	l 000 A		0.1		0
Gate-to-Source Charge	Q_GS	$V_{GS} = 4.5 \text{ V}, V_{DS} = 15 \text{ V}; I_D = 200 \text{ mA}$			0.2		nC
Gate-to-Drain Charge	Q_{GD}				0.1		
SWITCHING CHARACTERISTICS, $V_{GS} = 4$.	5 V (Note 4)						
Turn-On Delay Time	t _{d(ON)}				30		
Rise Time	t _r	V_{GS} = -4.5 V, V_{DD} = -15 V, I_D = -200 mA, R_G = 2.0 Ω			56		
Turn-Off Delay Time	t _{d(OFF)}				196		ns
Fall Time	t _f				145		

^{4.} Switching characteristics are independent of operating junction temperatures

NTNUS3171PZ

TYPICAL CHARACTERISTICS

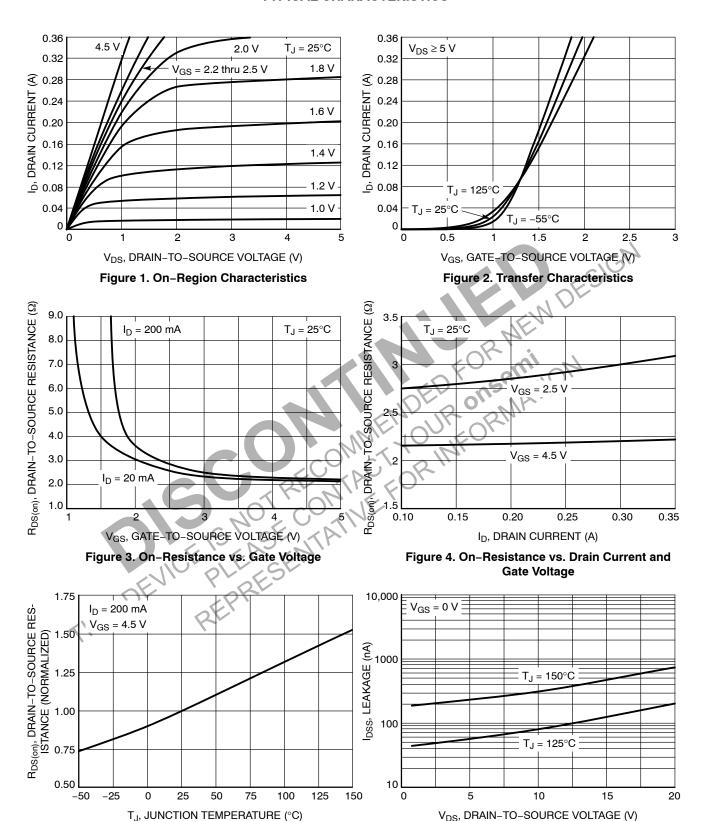


Figure 6. Drain-to-Source Leakage Current

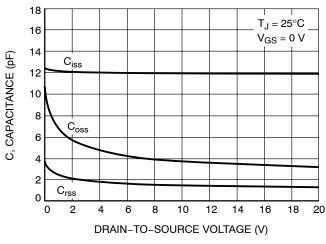
vs. Voltage

Figure 5. On-Resistance Variation with

Temperature

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TYPICAL CHARACTERISTICS



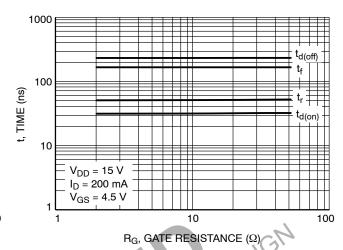
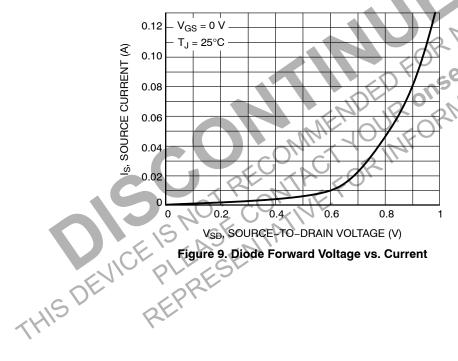


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance



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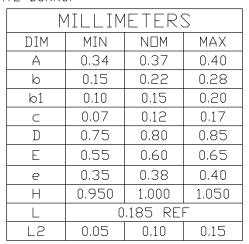


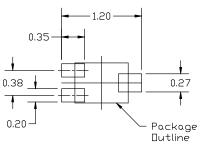
SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

DATE 18 JAN 2024

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
 DF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

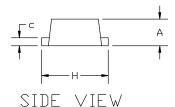


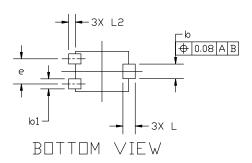


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

D	B
	E
TOP VIEW	





GENERIC MARKING DIAGRAM*



X = Specific Device Code

M = Date Code

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
COLLECTOR	3. CATHODE	CATHODE	3. ANODE	3. DRAIN

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DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1	

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